



100V DUAL PNP LOW SAT TRANSISTORS IN POWERDI5060-8

Features

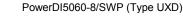
- BV_{CEO} > -100V
- I_C = -3A Continuous Collector Current
- I_{CM} = -8A Peak Pulse Current
- $R_{CE(SAT)} = 110m\Omega (Typ)$
- Rated to +175°C Ideal for High Ambient Temperature Environments
- Complementary Part DXTN3C100PD
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: POWERDI5060-8/SWP
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Lead-Frame;
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

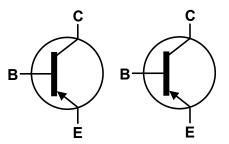
Applications

- Power Management
- Load Switches

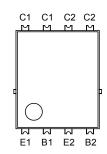








Internal Schematic



Top View Pin Configuration

Ordering Information

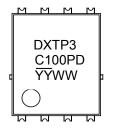
Product	Compliant	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per reel	
DXTP3C100PD-13	Standard	DXTP3C100PD	13	12	1,000	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI5060-8/SWP



DXTP3 = Product Type Marking Code C100PD = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 21 = 2021) WW = Week Code (01 to 53)



Absolute Maximum Ratings (@ TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Base Voltage	V _{EBO}	-7	V
Base Current	I _B	-0.5	А
Continuous Collector Current	Ic	-3	А
Peak Pulse Collector Current	I _{CM}	-8	А

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation (Notes		D-	1.76	W	
Linear Derating Factor	(Notes 6, 7)	P _D	11.7	mW/°C	
Thermal Resistance, Junction to Ambient	(Notes 5, 7)	Б	85		
Thermal Resistance, Junction to Ambient	(Notes 6, 7)	$R_{ hetaJA}$	37	°C/W	
Thermal Resistance, Junction to Lead (Note 8)		$R_{ heta JL}$	5.7		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C		

ESD Ratings (Note 9)

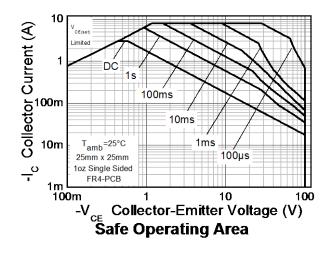
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

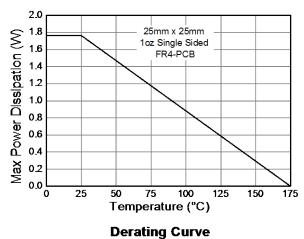
Notes:

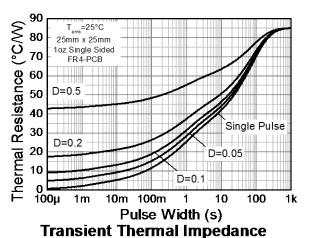
- 5. For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on single-sided 1.6mm FR4 PCB; device with one active die is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is measured at $t \le 5$ sec.
- 7. For a dual device with one active die.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

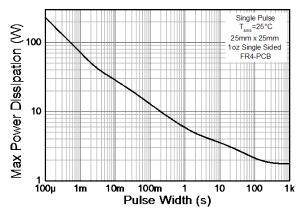


Thermal Characteristics and Derating Information









Pulse Power Dissipation



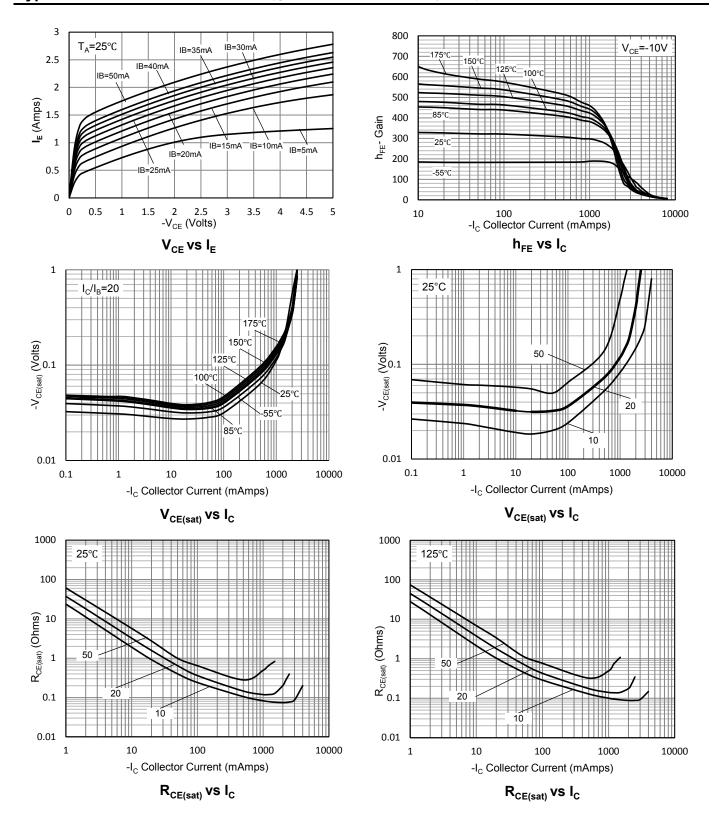
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-100	_	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-100	_	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	_	_	V	I _E = -100μA
Collector-Base Cutoff Current	1	_	_	-100	nA	V _{CB} = -80V
Collector-base Cuton Current	I _{CBO}	_	_	-50	μA	V _{CB} = -80V @Tj = 150°C
Emitter Cutoff Current	I _{EBO}	_	_	-100	nA	V _{EB} = -7V
Collector-Emitter Cutoff Current	ICES	_	_	-100	nA	V _{CES} = -80V
ON CHARACTERISTICS (Note 10)						
		170	305	_		I _C = -500mA, V _{CE} = -10V
DC Current Gain	h _{FE}	160	275	_		$I_C = -1A$, $V_{CE} = -10V$
Do Guilett Gaill	IIFE	45	90	_		$I_C = -2A$, $V_{CE} = -10V$
		10	20	_		$I_C = -3A$, $V_{CE} = -10V$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	-70	-110	mV	$I_C = -0.5A$, $I_B = -50mA$
Conector-Emitter Saturation Voltage		_	-220	-325		$I_C = -2A$, $I_B = -200mA$
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	110	180	mΩ	$I_C = -2A$, $I_B = -200mA$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	-0.91	-1	V	$I_C = -1A$, $I_B = -50mA$
Base-Entitle Saturation voltage		_	-1.02	-1.2	V	$I_C = -2A$, $I_B = -200mA$
Base-Emitter Turn-On Voltage	V _{BE(on)}	_	-0.68	-0.9	V	I _C = -0.1A, V _{CE} = -2V
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f⊤	_	100	_	MHz	V _{CE} = -10V, I _C = -100mA, f = 100MHz
Output Capacitance	C_{obo}	_	30	_	pF	V _{CB} = -10V, f = -1MHz
Delay Time	t _d	_	30	_	ns	
Rise Time	tr	_	30	_	ns	
Turn-On Time	t _{on}	_	60	_	ns	V _{CC} = -12.5V, I _C = -1A
Storage Time	ts	_	660	_	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$
Fall Time	t _f	_	50	_	ns	
Turn-Off Time	t _{off}	_	710	_	ns	

Note: 10. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

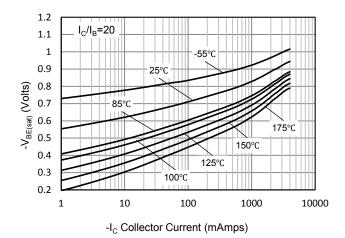


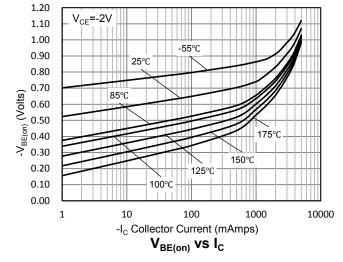
Typical Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)





PNP Typical Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.) (continued)



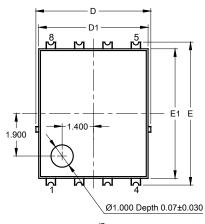


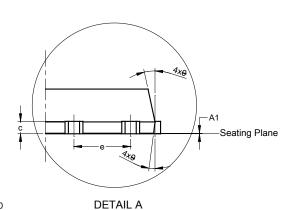


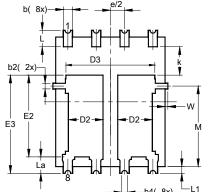
Package Outline Dimensions

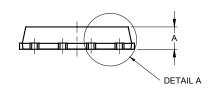
Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UXD)







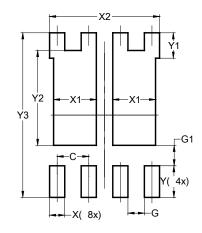


PowerDI5060-8/SWP						
(Type UXD)						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0.00	0.05				
b	0.30	0.50	0.41			
b2	0.20	0.35	0.25			
b4).25REF				
С	0.230	0.330	0.277			
D	5	.15 BS	\sim			
D1	4.70	5.10	4.90			
D2	1.46	1.66	1.55			
D3			3.98			
Е	6.40 BSC					
E1	5.60	6.00	5.80			
E2	3.46	3.86	3.66			
E2a	4.195	4.595	4.395			
е	1.27BSC					
k	1.05					
L	0.635	0.835	0.735			
La	0.635	0.835	0.735			
L1	0.200	0.400	0.300			
М	3.205	4.005	3.605			
W	0.025	0.225	0.125			
θ	10° 12° 11'					
θ1	θ1 6° 8° 7°					
All Dimensions in mm						

Suggested Pad Layout

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

PowerDI5060-8/SWP (Type UXD)



Dimensions	Value (in mm)		
	(111 111111)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	1.720		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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